

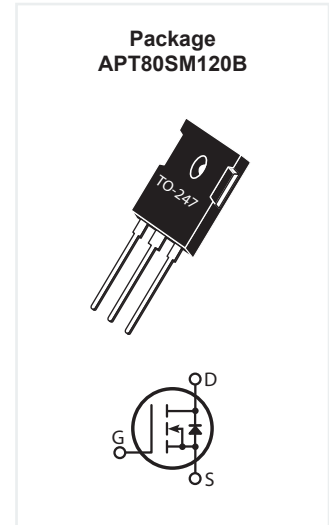
APT80SM120B

1200V, 80A, 40mΩ

Silicon Carbide N-Channel Power MOSFET

DESCRIPTION

Silicon carbide (SiC) power MOSFET product line from Microsemi increase your performance over silicon MOSFET and silicon IGBT solutions while lowering your total cost of ownership for high-voltage applications.



FEATURES / TYPICAL APPLICATIONS

SiC MOSFET Features:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_j(\text{max}) = +175\text{C}$
- Fast and reliable body diode
- Superior avalanche ruggedness

SiC MOSFET Benefits:

- High efficiency to enable lighter/compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need of external Free Wheeling Diode
- Lower system cost of ownership

Applications:

- PV inverter, converter and industrial motor drives
- Smart grid transmission & distribution
- Induction heating, and welding
- H/EV powertrain and EV charger
- Power supply and distribution

MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain Source Voltage	1200	V
I_{D}	Continuous Drain Current @ $T_c = 25^\circ\text{C}$	80	A
	Continuous Drain Current @ $T_c = 100^\circ\text{C}$	55	
I_{DM}	Pulsed Drain Current ^①	190	
V_{GS}	Gate-Source Voltage	-10 to +25	V
P_{D}	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	555	W
	Linear Derating Factor	3.7	W/°C

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta\text{JC}}$	Junction to Case Thermal Resistance		0.23	0.27	°C/W
T_j	Operating Junction Temperature	-55		175	°C
T_{stg}	Storage Junction Temperature Range	-55		150	
T_L	Soldering Temperature for 10 Seconds (1.6mm from case)			260	
Torque	Mounting Torque (TO-247 Package), 6-32 or M3 screw			10	in·lbf
				1.1	N·m

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STATIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	1200			V
$R_{DS(on)}$	Drain-Source On Resistance ^②	$V_{GS} = 20V, I_D = 40A$		40	55	m Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1mA$	1.7	3.0		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient			-5.0		mV/ $^{\circ}C$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200V$ $V_{GS} = 0V$			100	μA
		$T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$			500	
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = +20V / -10V$			± 100	nA

$T_J = 25^{\circ}C$ unless otherwise specified

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DD} = 1000V$ $f = 1MHz$		3850		pF
C_{riss}	Reverse Transfer Capacitance			25		
C_{oss}	Output Capacitance			220		
Q_g	Total Gate Charge	$V_{GS} = 0/20V$		220		nC
Q_{gs}	Gate-Source Charge	$V_{DD} = 800V$		40		
Q_{gd}	Gate-Drain Charge	$I_D = 40A$		60		
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 800V$		17		ns
t_r	Current Rise Time	$V_{GS} = 0/20V$		10		
$t_{d(off)}$	Turn-Off Delay Time	$I_D = 40A$		45		
t_f	Current Fall Time	$R_G = 3.0 \Omega$ ^③		25		
E_{on2}	Turn-On Switching Energy ^④	$L = 115 \mu H$ $T_C = 25^{\circ}C$		1100		
E_{off}	Turn-Off Switching Energy	Freewheeling Diode = APT20SCE120B		300		
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 466V$		15		ns
t_r	Current Rise Time	$V_{GS} = 0/20V$		10		
$t_{d(off)}$	Turn-Off Delay Time	$I_D = 30A$		50		
t_f	Current Fall Time	$R_G = 3.0 \Omega$ ^③		25		
E_{on2}	Turn-On Switching Energy ^④	$L = 115 \mu H$ $T_C = 150^{\circ}C$		1030		
E_{off}	Turn-Off Switching Energy	Freewheeling Diode = APT20SCE120B		430		
ESR	Equivalent Series Resistance	$f = 1MHz, 25mV, \text{Drain Short}$		0.58		Ω
SCWT	Short Circuit Withstand Time	$V_{DS} = 960V, V_{GS} = 20V, T_C = 25^{\circ}C$		4		μS
E_{AS}	Avalanche Energy, Single Pulse	$V_{DS} = 145V, V_{GS} = 20V, I_D = 40A, T_C = 25^{\circ}C$		3500		mJ

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode Forward Voltage	$I_{SD} = 40A, V_{GS} = 0V$		3.7		V
t_{rr}	Reverse Recovery Time	$I_{SD} = 40A, V_{DD} = 800V$ $di/dt = -1000A/\mu s$		80		ns
Q_{rr}	Reverse Recovery Charge			540		nC
I_{rrm}	Reverse Recovery Current			12.2		A

$T_J = 25^{\circ}C$ unless otherwise specified

- ① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature
 ② Pulse test: Pulse Width < 380 μs , duty cycle < 2%.
 ③ R_G is total gate resistance including internal gate driver impedance.
 ④ E_{on2} includes energy of APT20SCE120B free wheeling diode.

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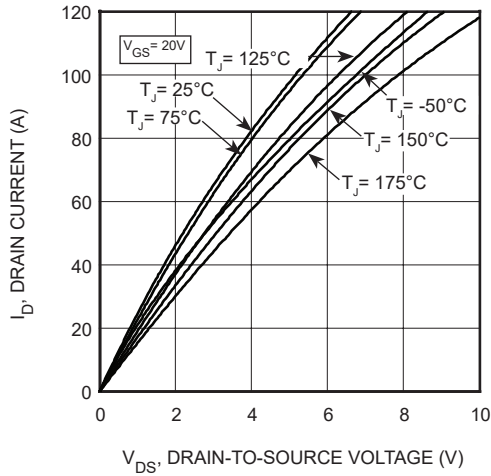


Figure 1, Output Characteristics

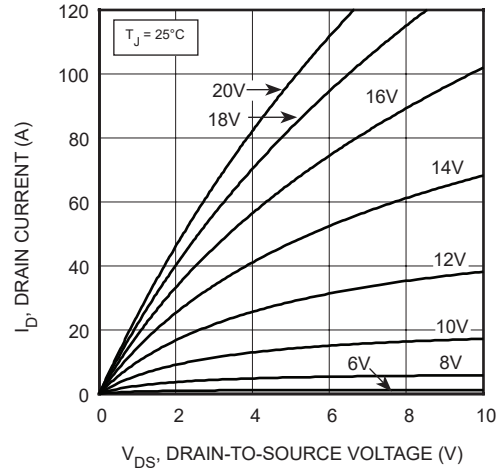


Figure 2, Output Characteristics

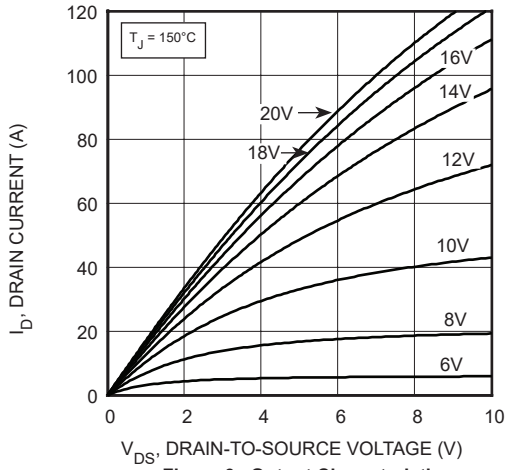


Figure 3, Output Characteristics

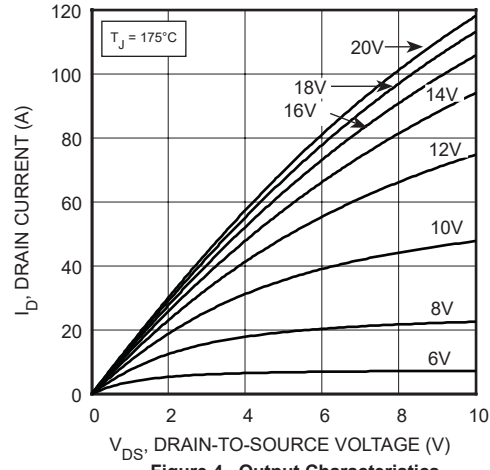


Figure 4, Output Characteristics

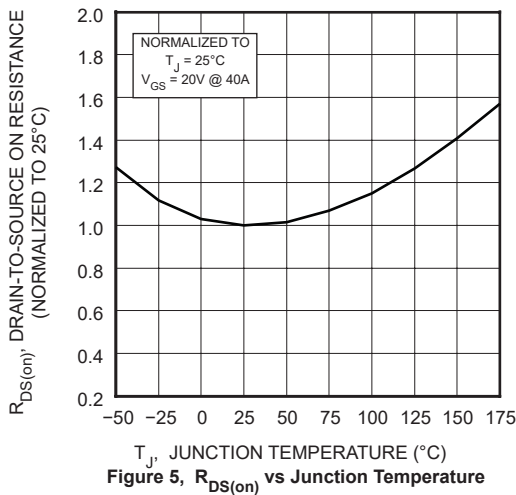


Figure 5, $R_{DS(on)}$ vs Junction Temperature

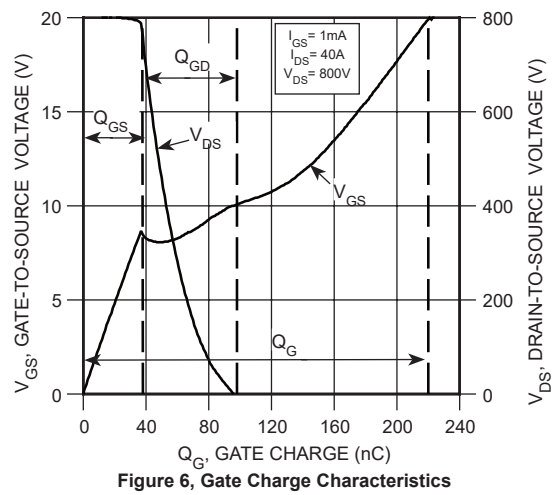


Figure 6, Gate Charge Characteristics

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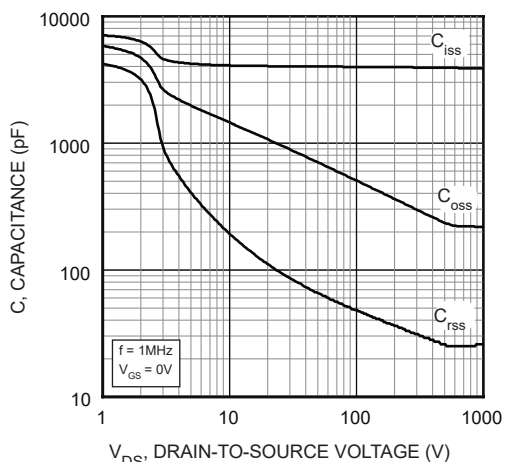


Figure 7, Capacitance vs Drain-to-Source Voltage

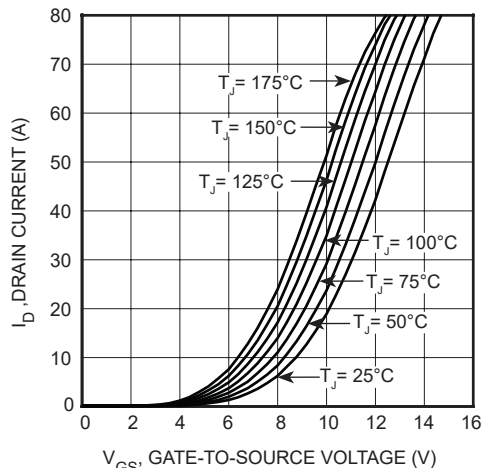


Figure 8, Output Characteristics I_D vs V_{GS} Temperature

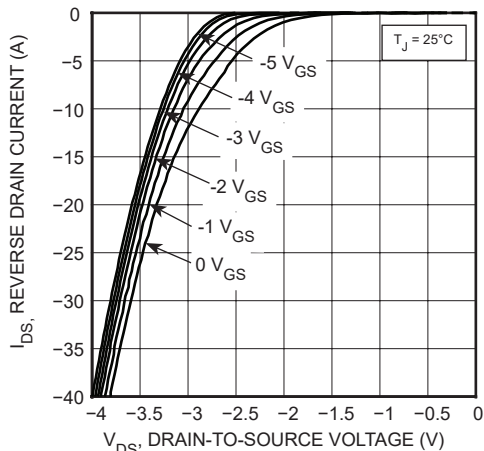


Figure 9, Reverse Drain Current vs Drain-to-Source Voltage Third Quadrant Conduction

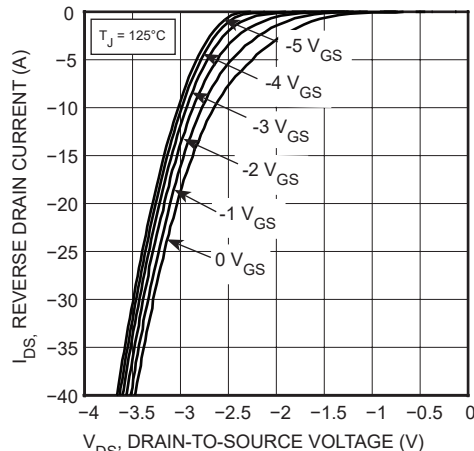


Figure 10, Reverse Drain Current vs Drain-to-Source Voltage Third Quadrant Conduction

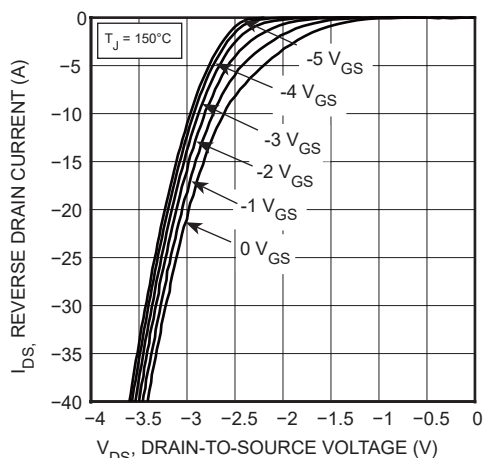


Figure 11, Reverse Drain Current vs Drain-to-Source Voltage Third Quadrant Conduction

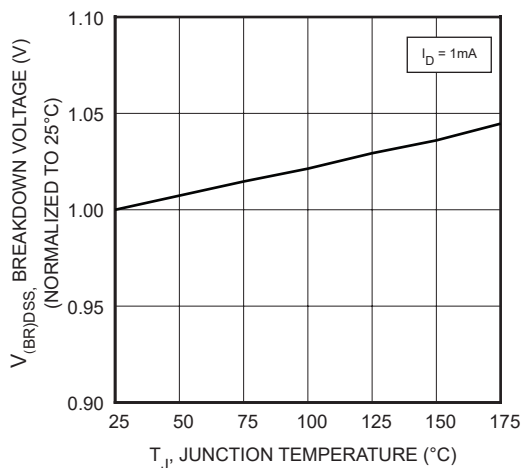


Figure 12, Breakdown Voltage vs Temperature

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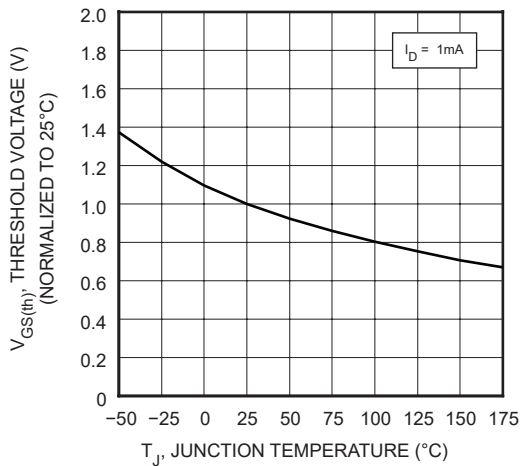


Figure 13, Threshold Voltage vs Temperature

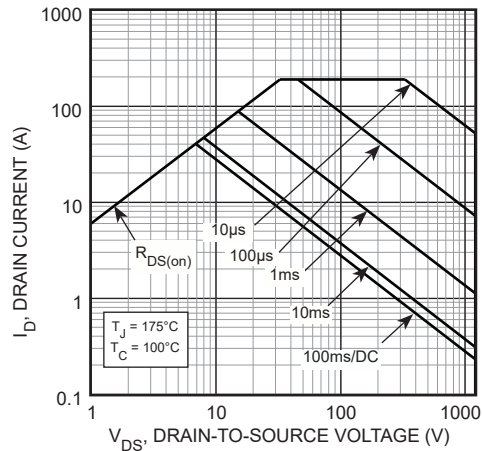


Figure 14, Forward Safe Operating Area

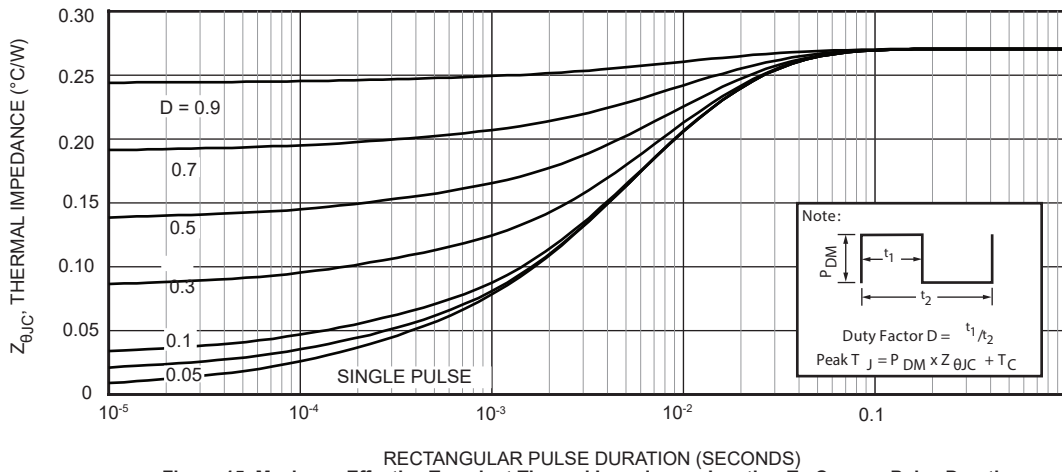
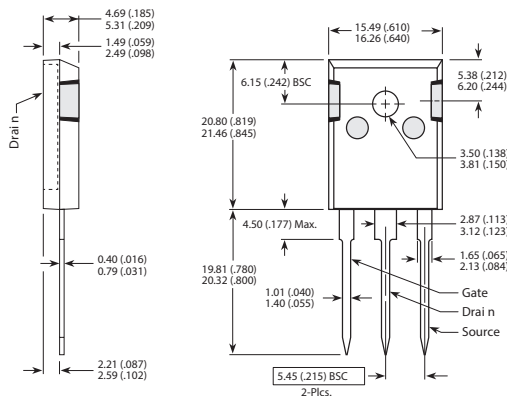


Figure 15, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

TO-247 (B) Package Outline



Dimensions in Millimeters (Inches)

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